

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	445	(excimer near laser) near25 (polysilicon)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/09/22 14:25	
2	BRS	L2	47	(excimer near laser) near25 (polysilicon) near25 (grain)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/09/22 14:33	
3	BRS	L3	49	(excimer) near25 (polysilicon) near25 (grain)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/09/22 14:33	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	20	(excimer) near25 (polysilicon) near25 (grain) near35 (amorphous)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:35	
5	BRS	L5	4	(excimer) near25 (poly\$5) near25 (grain) near35 (amorphous)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:36	
6	BRS	L6	69	(excimer) near25 (poly\$5) near25 (grain)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:38	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	52	(excimer) near25 (poly-\$5) near25 (grain)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:40	
8	BRS	L8	14773	(amorphous) near35 (region)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:40	
9	BRS	L9	5481	(amorphous) near35 (region) near25 (crystal\$5)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/09/22 14:41	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	5481	(amorphous) near35 (region\$1 or portion41) near25 (crystal\$5)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/09/22 14:41	
11	BRS	L11	63	(amorphous) near35 (region\$1 or portion41) near25 (crystal\$5) near35 (excimer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/09/22 14:41	

	U	1	Document ID	Title	Current OR	Pages
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020110964 A1	RECRYSTALLIZATION METHOD OF POLYSILICON FILM IN THIN FILM TRANSISTOR	438/166	12
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6716726 B2	Thin film semiconductor device containing polycrystalline Si--Ge alloy and method for producing thereof	438/487	20
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6432758 B1	Recrystallization method of polysilicon film in thin film transistor	438/166	11
4	<input type="checkbox"/>	<input type="checkbox"/>	TW 578310 A	Low temperature poly silicon thin film transistor and method of forming poly silicon layer of the same		1